

### **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing Of Claims:**

1-9. (Canceled)

10. (New) A method for producing a micromechanical component using a sacrificial layer, comprising:

producing a patterned porous region in a silicon substrate;  
producing a functional layer above the porous region; and  
subsequently exposing the functional layer, the porous region being used at least partially as the sacrificial layer.

11. (New) The method as recited in Claim 10, wherein the porous region is produced first and then the functional layer.

12. (New) The method as recited in Claim 10, wherein:

the step of producing the porous region includes producing a doped first region in the substrate in which no pores will form, and subsequently producing the porous region.

13. (New) The method as recited in Claim 10, further comprising:

patterning the functional layer; and  
producing additional layers above the porous region, the additional layers cooperating with the functional layer and being provided in patterned form.

14. (New) The method as recited in Claim 10, further comprising:

etching off in a dry-chemical manner the porous region below the functional layer.

15. (New) The method as recited in Claim 10, wherein:

the porous region includes a first porous partial region and a second porous partial region,

the second porous partial region has a higher porosity than the first porous partial region,

a cavity is formed in the second porous partial region by a thermal treatment, and a cover layer remains in the first porous partial region.

16. (New) The method as recited in Claim 15, further comprising:  
in order to expose the functional layer, etching off at least the cover layer at least partially.
17. (New) The method as recited in Claim 10, wherein:  
the functional layer is produced first and the porous region below the functional layer is produced subsequently.
18. (New) A micromechanical component, comprising:  
a silicon substrate; and  
a functional layer arranged above the porous region, the functional layer having been exposed through a removal of a patterned porous region serving as a sacrificial layer and above which the functional layer was produced.